

CLEAN COPY OF THE CLAIMS AS AMENDED

- 1 (Amended). An etch mixture for silicon consisting essentially of a fluorine-containing gas selected from the group consisting of SF_6 , Si_2F_6 and SiF_4 together with HBr and oxygen.
2. An etch mixture according to claim 1 wherein the mixture additionally includes a noble gas.
3. An etch mixture according to claim 1 wherein the mixture contains SF_6 .
4. An etch mixture according to claim 3 wherein the mixture additionally includes Si_2F_6 and SiF_4 .
5. An etch mixture according to claim 3 wherein the volume ratio of $\text{HBr}:\text{SF}_6$ is 0.1 to 10.
6. An etch mixture according to claim 3 wherein the volume ratio of HBr and $\text{SF}_6:\text{O}_2$ is 0.1 to 10.

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